

SANYO	No.1856A	2SA1435
		PNP Epitaxial Planar Silicon Transistor

High- h_{FE} , AF Amp Applications

Applications

- . Low frequency general-purpose amplifiers, drivers, muting circuits

Features

- . Adoption of MBIT process
- . High DC current gain ($h_{FE}=500$ to 1200)
- . Large current capacity
- . Low collector-to-emitter saturation voltage ($V_{CE(sat)} \leq 0.5V$ max)
- . High V_{EBO} ($V_{EBO} \geq 15V$)

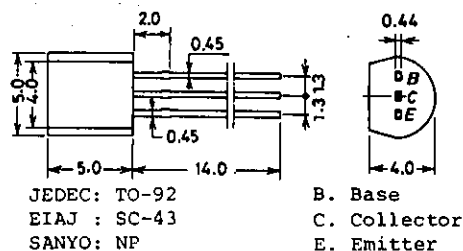
Absolute Maximum Ratings at Ta=25°C

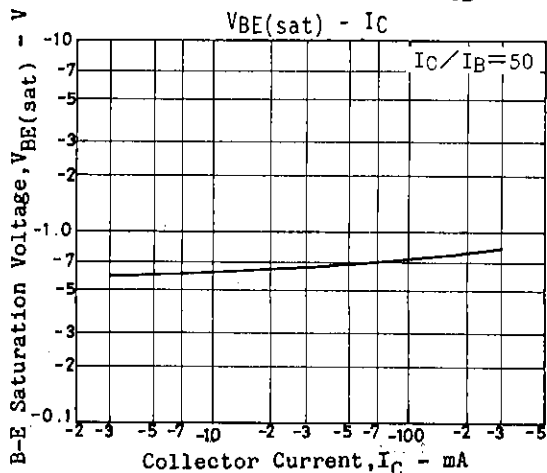
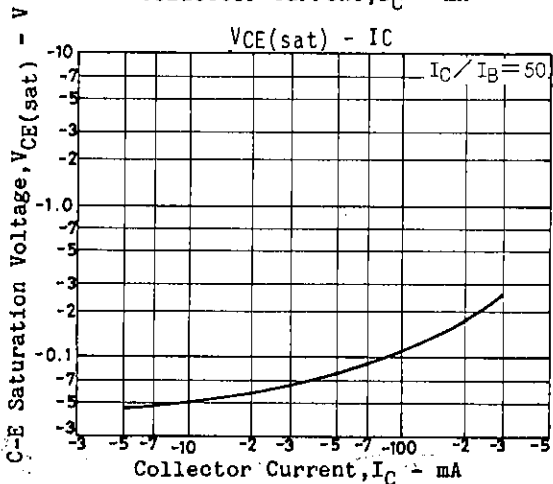
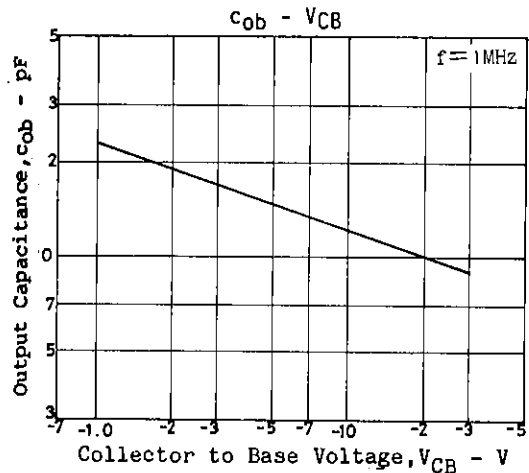
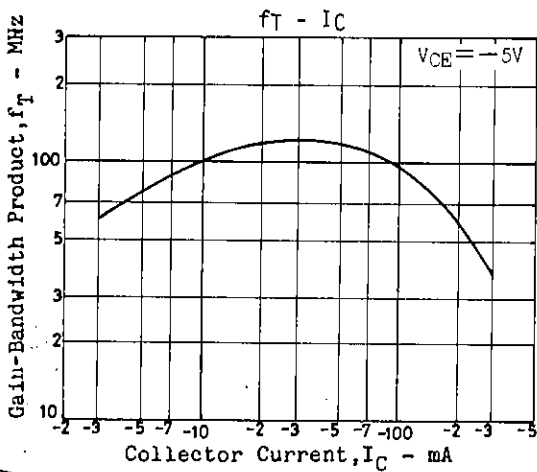
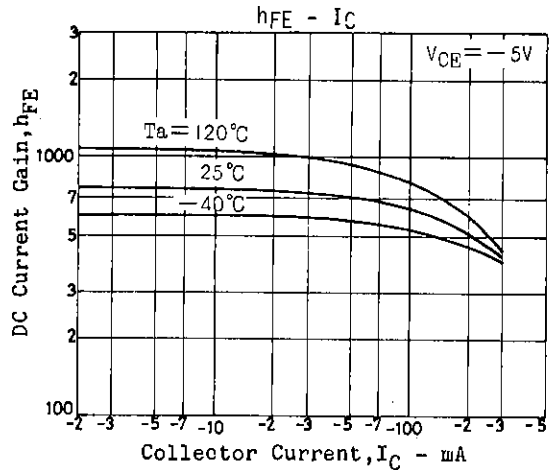
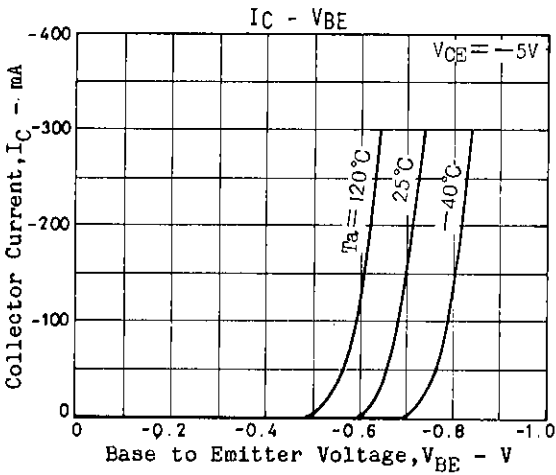
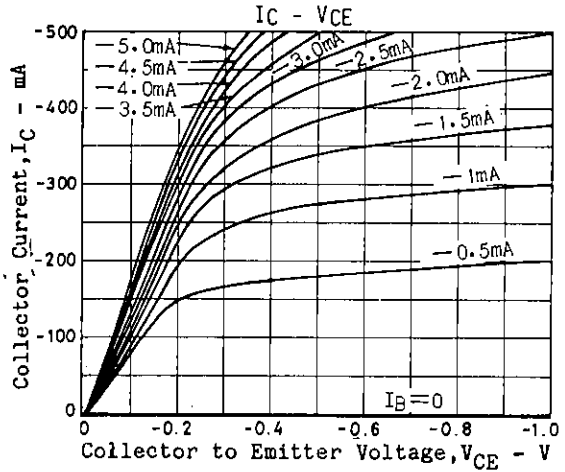
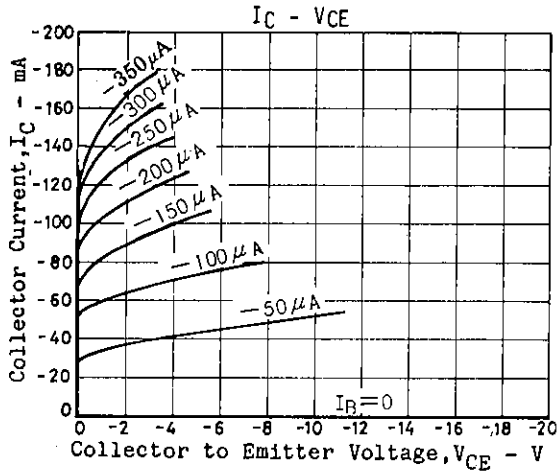
Collector to Base Voltage	V_{CB0}	-30	V
Collector to Emitter Voltage	V_{CEO}	-25	V
Emitter to Base Voltage	V_{EBO}	-15	V
Collector Current	I_C	-300	mA
Collector Current(Pulse)	I_{CP}	-500	mA
Collector Dissipation	P_C	600	mW
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55 to 150	°C

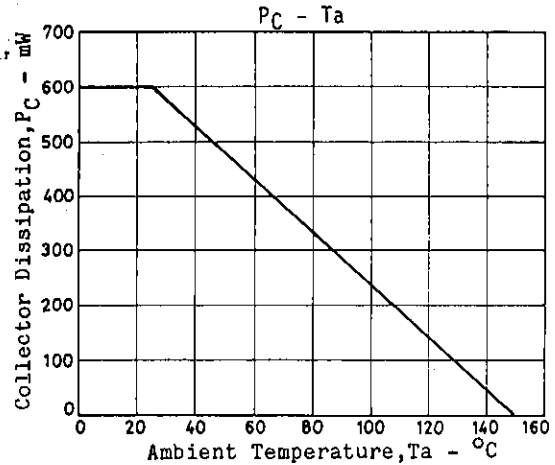
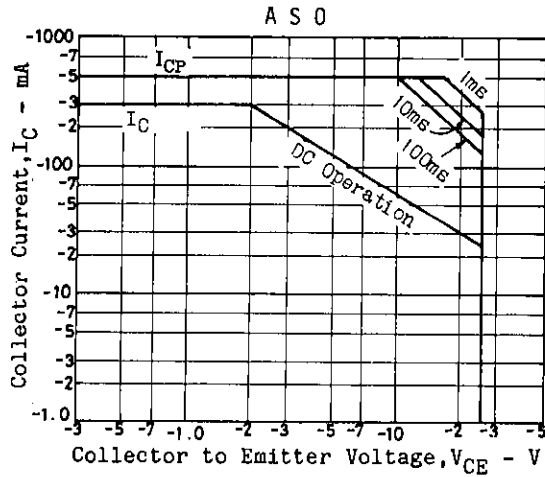
Electrical Characteristics at Ta=25°C

			min	typ	max	unit
Collector Cutoff Current	I_{CB0}	$V_{CB}=-20V, I_E=0$			-0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=-10V, I_C=0$			-0.1	μA
DC Current Gain	$h_{FE}(1)$	$V_{CE}=-5V, I_C=-10mA$	500	800	1200	
	$h_{FE}(2)$	$V_{CE}=-5V, I_C=-200mA$	200			
Gain-Bandwidth Product	f_T	$V_{CE}=-10V, I_C=-10mA$		100		MHz
Output Capacitance	c_{ob}	$V_{CB}=-10V, f=1MHz$		12		pF
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-200mA, I_B=-4mA$	-0.18		-0.5	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=-200mA, I_B=-4mA$	-0.77		-1.1	V
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=-10\mu A, I_E=0$	-30			V
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=-1mA, R_{BE}=\infty$	-25			V
Emitter to Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=-10\mu A, I_C=0$	-15			V

Package Dimensions 2003A
(unit: mm)







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